Low-Voltage Circuits in Floating-Gate and Double-Gate CMOS

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Mixed Analog-Digital VLSI Circuits and Systems Lab

- **Research focus**: Low-voltage/low-power analog and mixed-signal circuit design
- Current M.S./Ph.D. students:

Sunitha Bandla, Abhishek Kammula, Eric McDonald, Kofi Odame, Sheng-Yu Peng

• Former M.S./Ph.D. students:

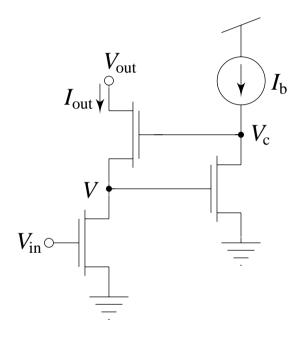
Karan Mathur, Mark Neidengard, Yuan Yang

- Current projects:
 - High-level synthesis of translinear and log-domain circuits and systems
 - Floating-gate MOS (FGMOS) circuit design
 - Double-gate MOS (DGMOS) modelling and circuit design
 - Chemical sensing with chemoreceiptive neuron MOS (CvMOS) transistors





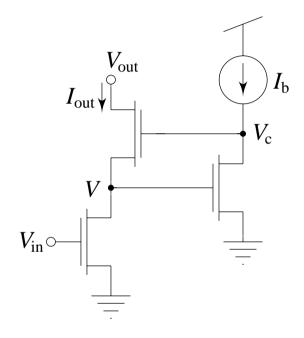
• Säckinger's regulated cascode circuit has a very high incremental R_{out} .







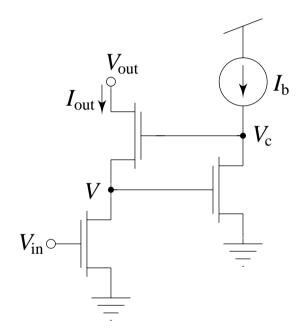
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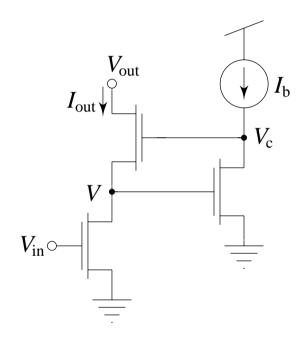
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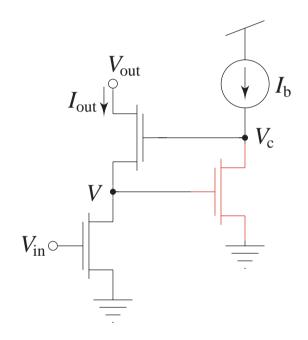
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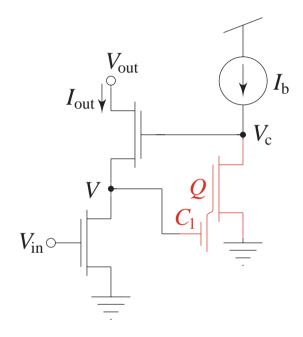
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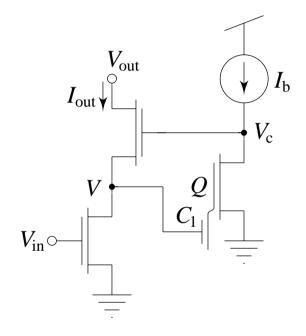
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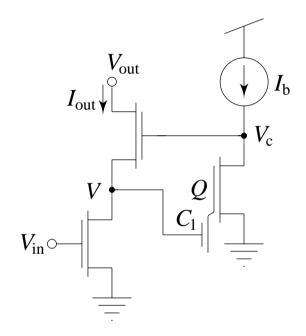
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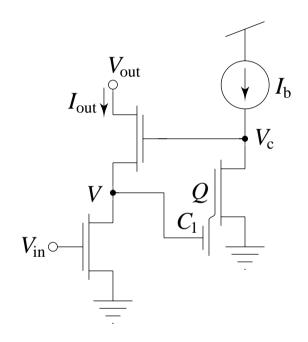
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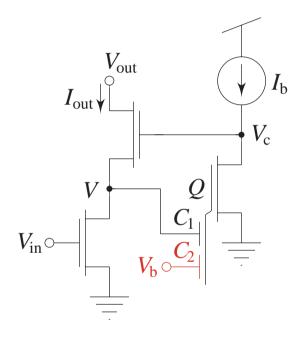
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- Not robust to drift in Q, or changes in I_b or temperature.







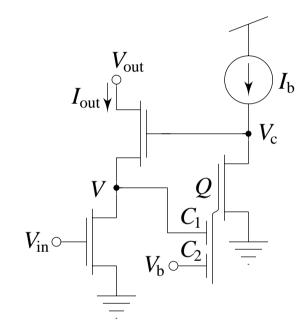
• We can add a second control gate and make $V \approx V_{\text{DSsat}}$ by adjusting V_{b} rather than Q.







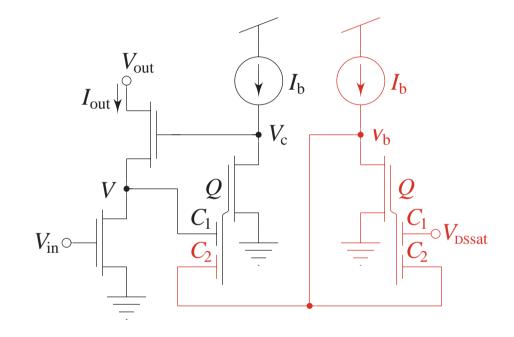
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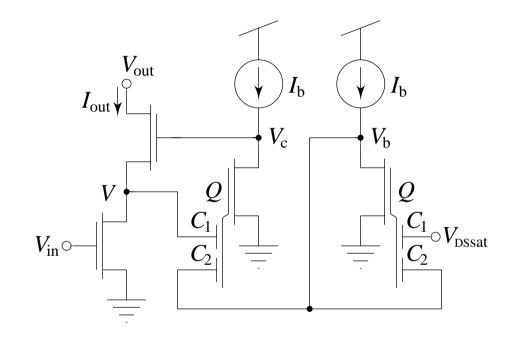
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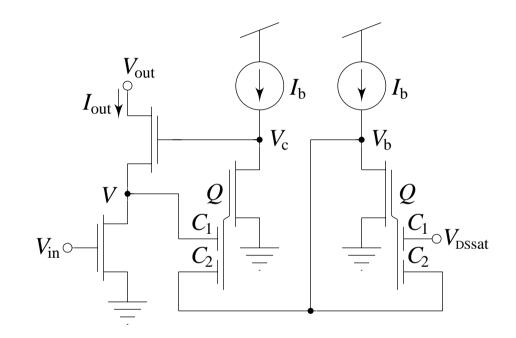
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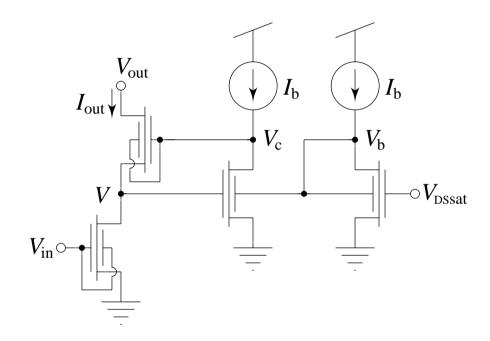
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- One V_b generator can be shared by multiple regulated cascodes.







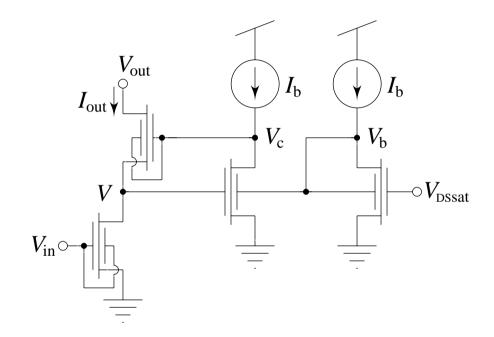
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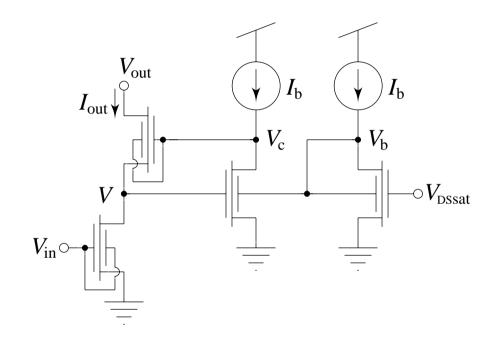
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- Desirable for the threshold voltages of the front and back gates to both be positive.

